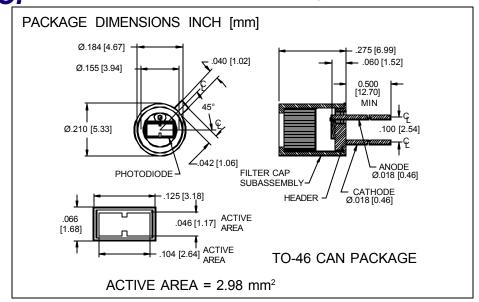
# **PHOTONIC** Silicon Photodiode, Filter Combination Photoconductive **DETECTORS INC.** 500 nm (blue color) Type PDV-C405-46





RESPONSIVITY (A/W)

#### **FEATURES**

- 500 nm CWL
- 70 nm FWHM
- Large active area

### **DESCRIPTION**

The **PDV-C405-46** is a silicon, PIN planar diffused, photodiode with a blue color 500 nm +/- 2 nm CWL wide band interference filter and a wide 70 nm half bandwidth. Ideal for color meters, & photometry and radiometry measurment applications.

### **APPLICATIONS**

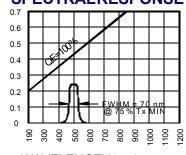
- Blue color matching
- Color meters
- Film processing

## ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

SYMBOL	PARAMETER	MIN	MAX	UNITS
V <sub>BR</sub>	Reverse Voltage		100	V
T <sub>STG</sub>	Storage Temperature	-20	+85	⊙C
To	Operating Temperature Range	-15	+70	⊙C
Ts	Soldering Temperature*		+240	∘C
I <sub>L</sub>	Light Current		500	mA

<sup>\*1/16</sup> inch from case for 3 secs max

## **SPECTRALRESPONSE**



WAVELENGTH(nm)

## ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	MIN	TYP	MAX	UNITS
Isc	Short Circuit Current***	H = 100 fc, 2850 K	40	45		$\mu$ A
ΙD	Dark Current	H = 0, V <sub>R</sub> = 10 V		.15	1.0	nA
RsH	Shunt Resistance	H = 0, V <sub>R</sub> = 10 mV	.5	1.0		GΩ
TC Rsh	Rsh Temp. Coefficient	H = 0, V <sub>R</sub> = 10 mV		-8		% / °C
Сл	Junction Capacitance	H = 0, V <sub>R</sub> = 10 V**		10		рF
CWL	Center Wavelength	(CWL, $\lambda$ o) +/- 2 nm		500		nm
HBW	Half Bandwidth	(FWHM)		70		nm
VBR	Breakdown Voltage	I = 10 μA	70	100		V
NEP	Noise Equivalent Power	V <sub>R</sub> = 10 V @ Peak		1.5x10 <sup>-14</sup>		W/√ <sub>Hz</sub>
tr	Response Time	RL = 1 KΩ V <sub>R</sub> = 50 V		10		nS

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.\*\*f=1MHz, \*\*\*without filter [FORM NO. 100-PDV-C405-46 REV N/C]